

N-channel 30 V, 0.0072 Ω typ., 48 A STripFET™ V Power MOSFET in a DPAK package

Datasheet - not recommended for new design

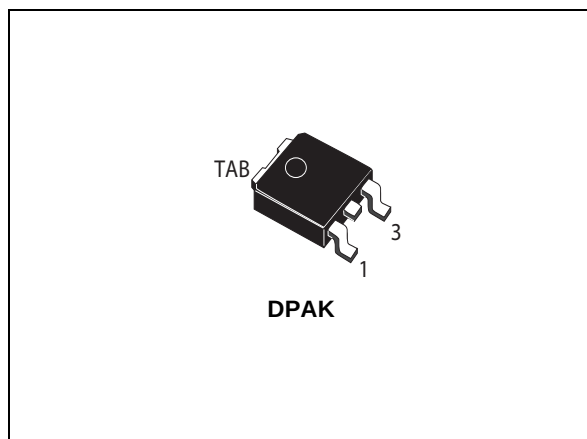
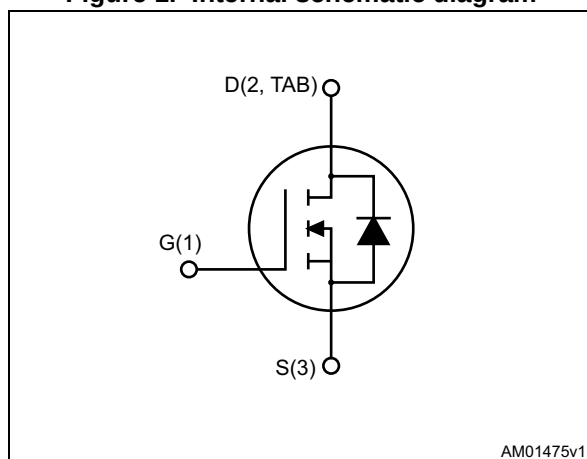


Figure 1. Internal schematic diagram



Features

Order code	V_{DS} @ T_{jmax}	$R_{DS(on)}$ max	I_D
STD60N3LH5	35 V	0.008 Ω	48 A

- $R_{DS(on)} * Q_g$ industry benchmark
- Extremely low on-resistance $R_{DS(on)}$
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using STMicroelectronics' STripFET™V technology. The device has been optimized to achieve very low on-state resistance, contributing to a FOM that is among the best in its class.

Table 1. Device summary

Order code	Marking	Packages	Packaging
STD60N3LH5	60N3LH5	DPAK	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	30	V
V_{DS}	Drain-source voltage @ T_{jmax}	35	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	48	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	42.8	A
$I_{DM}^{(2)}$	Drain current (pulsed)	192	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	60	W
	Derating factor	0.4	W/ $^{\circ}\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	160	mJ
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 175	$^{\circ}\text{C}$

1. Limited by wire bonding.
2. Pulse width limited by safe operating area.
3. Starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = 24\text{ A}$, $V_{DD} = 12\text{ V}$.

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max.	2.5	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max.	50	$^{\circ}\text{C/W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 30\text{ V}$ $V_{DS} = 30\text{ V}$, $T_C = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1	1.8	3	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 24\text{ A}$		0.0072	0.008	Ω
		$V_{GS} = 5\text{ V}$, $I_D = 24\text{ A}$		0.0088	0.011	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1350	1620	pF
C_{oss}	Output capacitance		-	265	318	pF
C_{rss}	Reverse transfer capacitance		-	32	38	pF
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 48\text{ A}$ $V_{GS} = 5\text{ V}$ (Figure 14)	-	8.8	12.3	nC
Q_{gs}	Gate-source charge		-	4.7	6.6	nC
Q_{gd}	Gate-drain charge		-	2.2	3.1	nC
Q_{gs1}	Pre V_{th} gate-to-source charge	$V_{DD} = 15\text{ V}$, $I_D = 48\text{ A}$ $V_{GS} = 5\text{ V}$ (Figure 19)	-	2.2	3.1	nC
Q_{gs2}	Post V_{th} gate-to-source charge		-	2.5	3.5	nC
R_G	Gate input resistance	$f = 1\text{ MHz}$, gate DC Bias = 0, test signal level = 20 mV, $I_D = 0$	-	1.1	1.3	Ω

Table 6. Switching on/off (resistive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=10\text{ V}$, $I_D=24\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (<i>Figure 13</i> and <i>Figure 18</i>)	-	6	-	ns
t_r	Rise time		-	33	-	ns
$t_{d(off)}$	Turn-off delay time		-	19	-	ns
t_f	Fall time		-	4.2	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		48	A
I_{SDM}	Source-drain current (pulsed) ⁽¹⁾		-		192	A
V_{SD}	Forward on voltage	$I_{SD}=24\text{ A}$, $V_{GS}=0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD}=48\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=20\text{ V}$, (<i>Figure 15</i>)	-	25		ns
Q_{rr}	Reverse recovery charge		-	18.5		nC
I_{RRM}	Reverse recovery current		-	1.5		A

1. Pulsed: pulse duration = 300 μ s, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

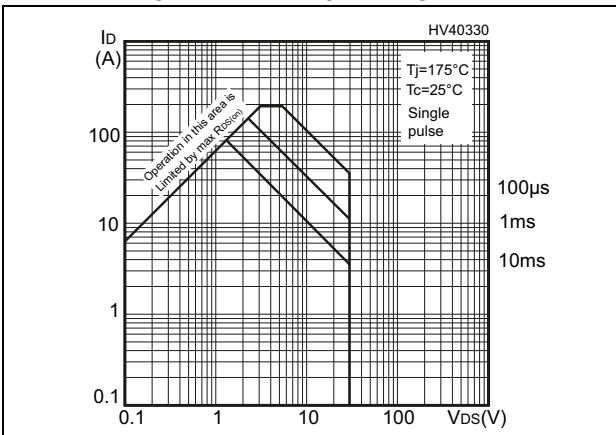


Figure 3. Thermal impedance

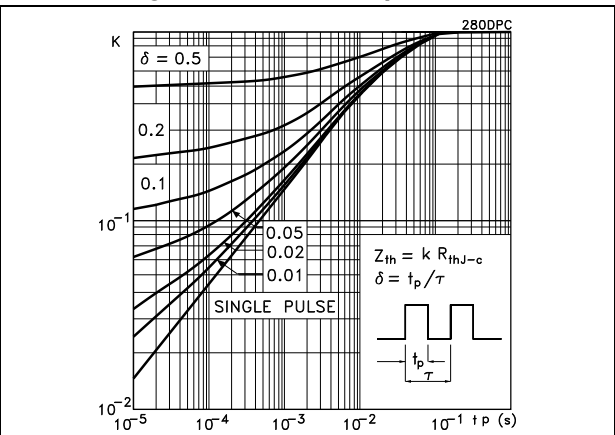


Figure 4. Output characteristics

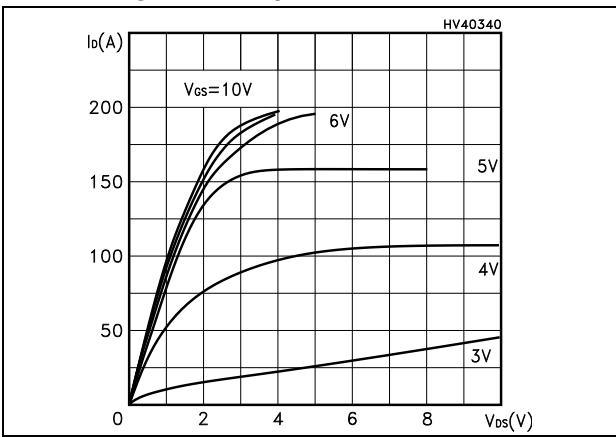


Figure 5. Transfer characteristics

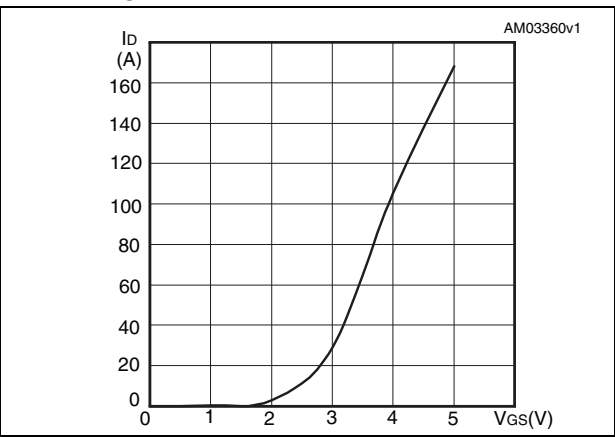


Figure 6. Normalized $V_{(BR)DSS}$ vs temperature

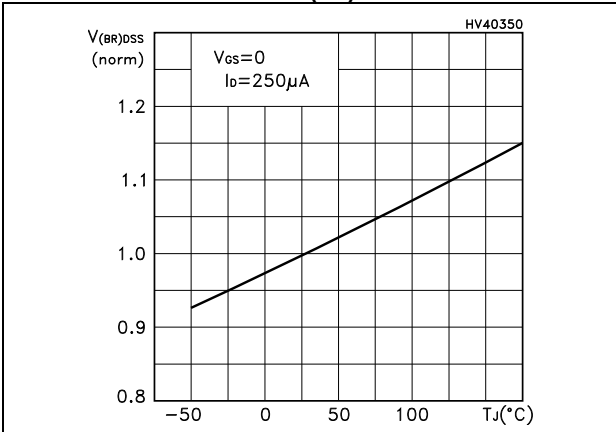


Figure 7. Static drain-source on-resistance

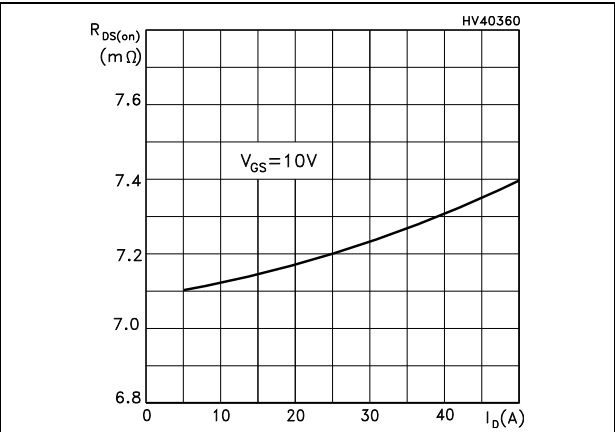


Figure 8. Gate charge vs gate-source voltage

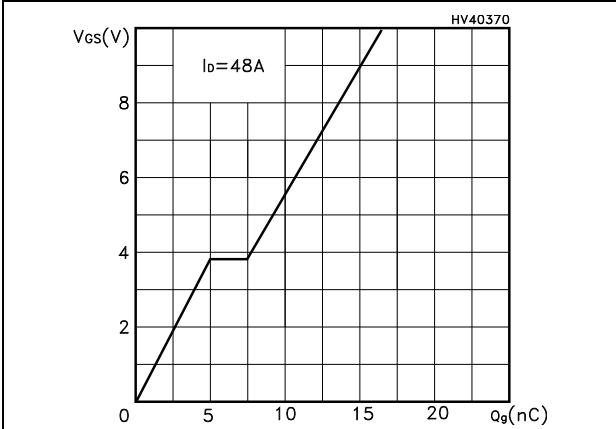


Figure 9. Capacitance variations

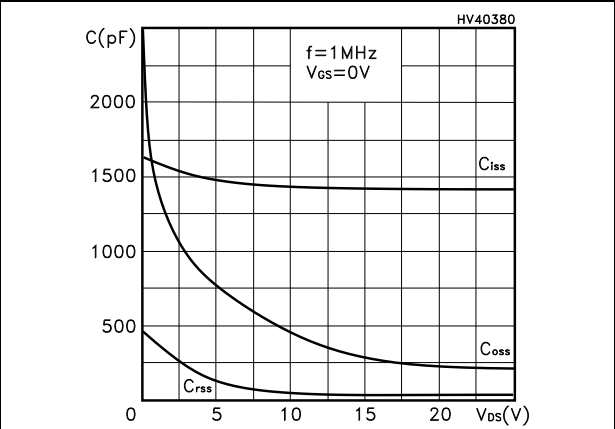


Figure 10. Normalized gate threshold voltage vs temperature

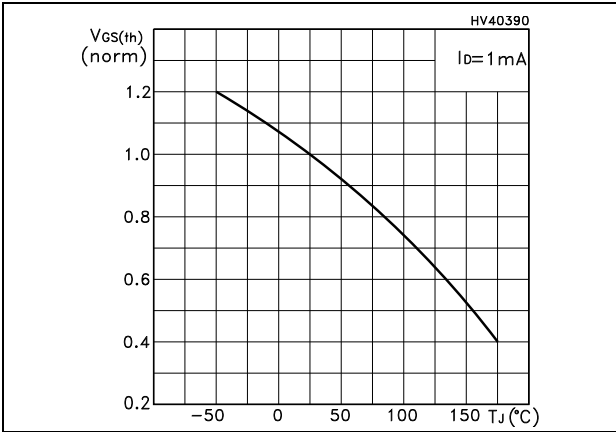


Figure 11. Normalized on-resistance vs temperature

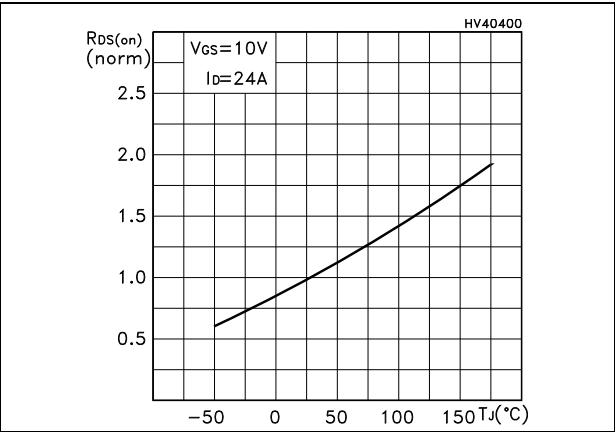


Figure 12. Source-drain diode forward characteristics

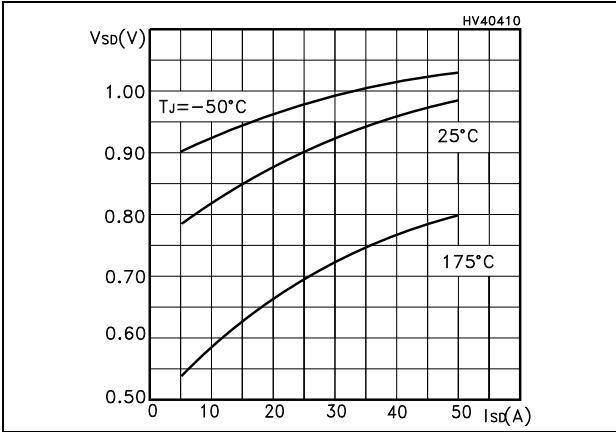
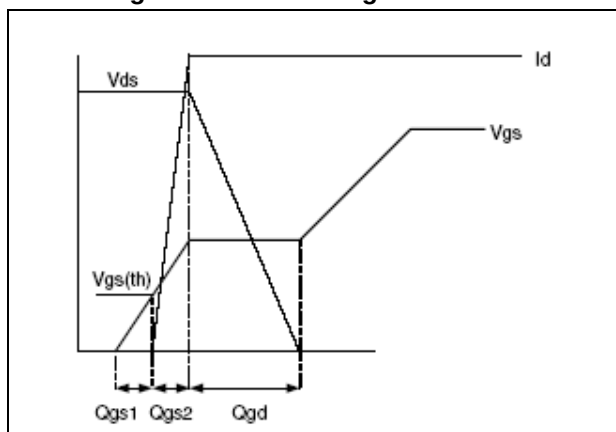


Figure 19. Gate charge waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 20. DPAK (TO-252) type A drawing

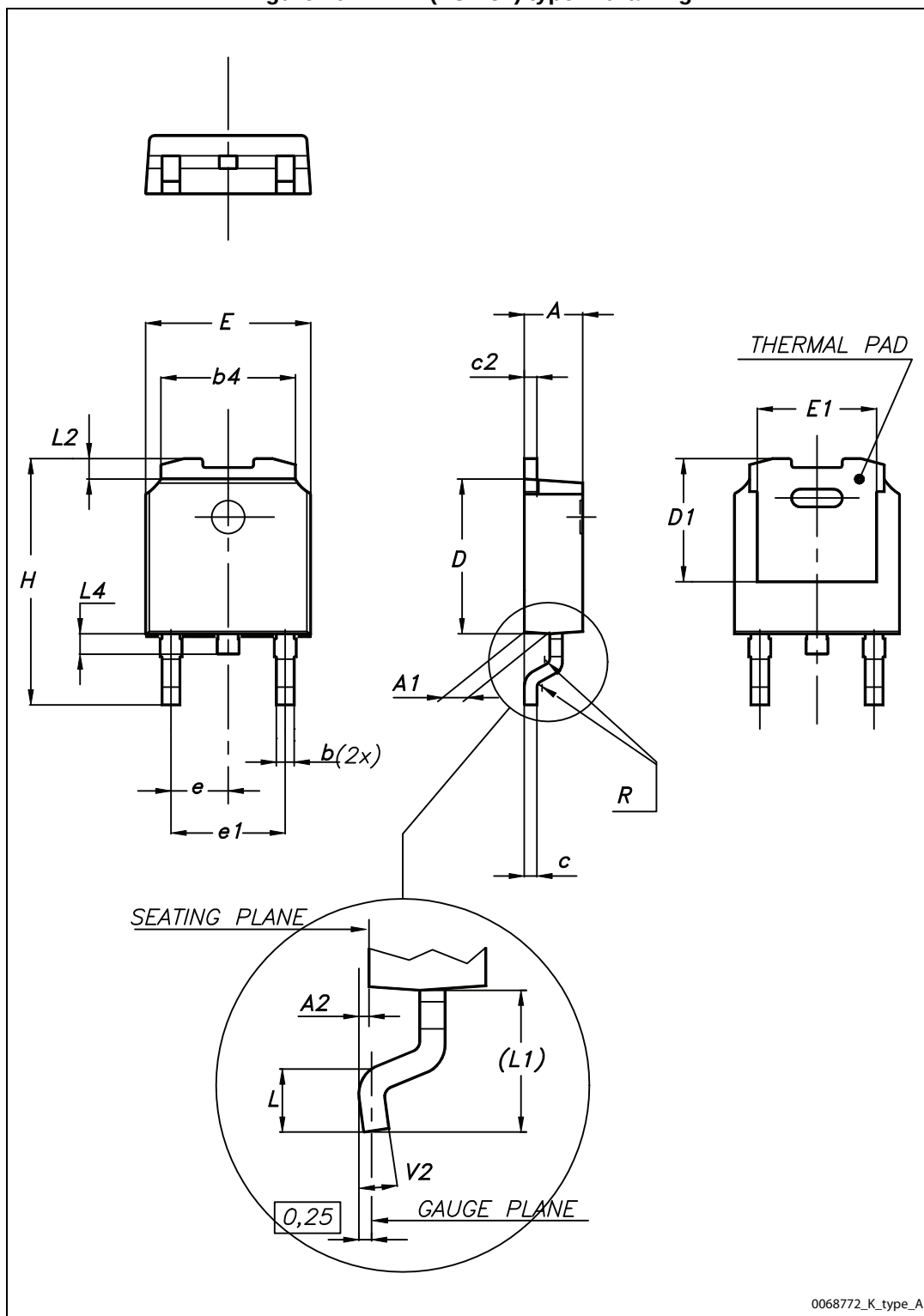


Table 9. DPAK (TO-252) type E mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 21. DPAK (TO-252) type E drawing

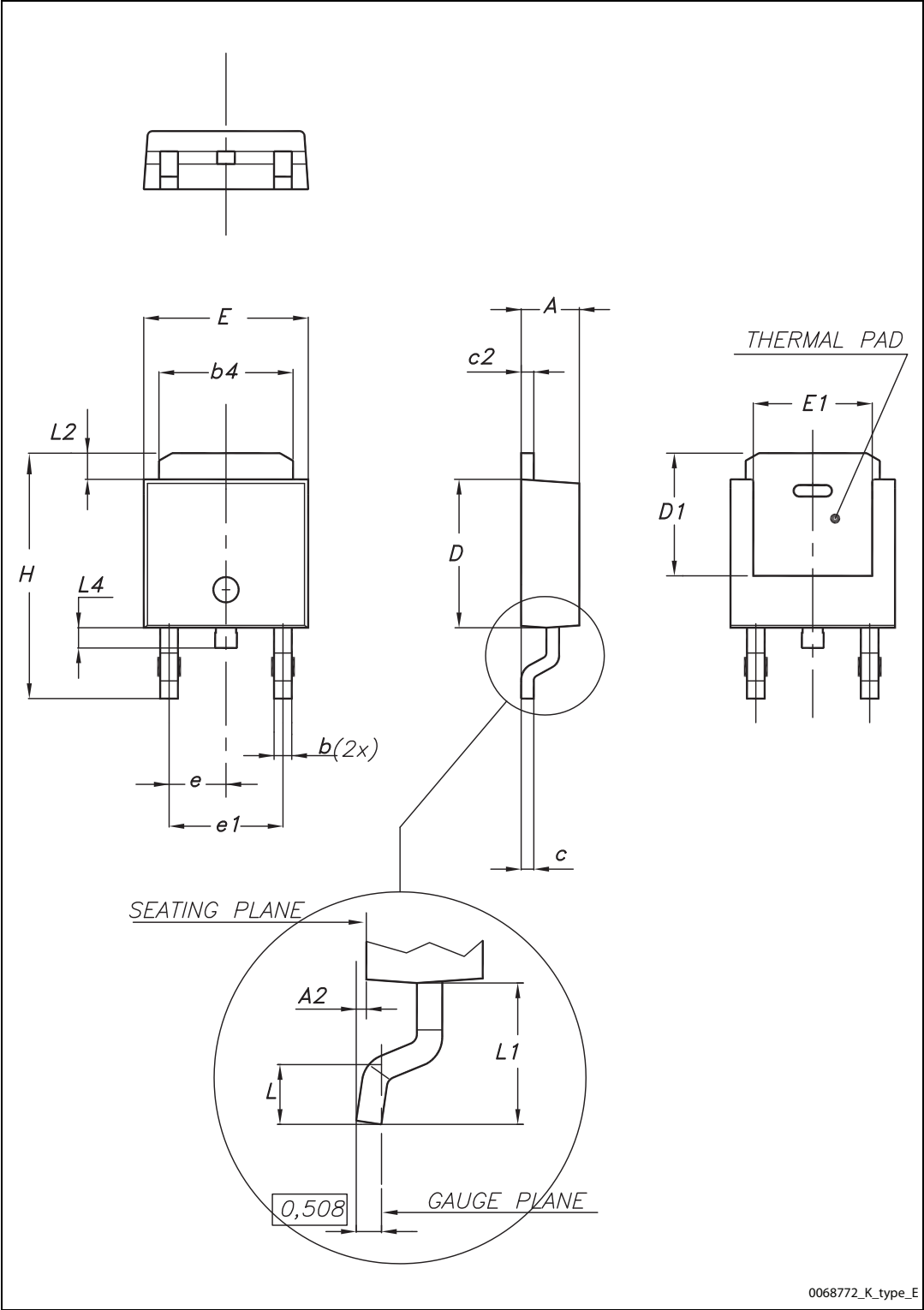
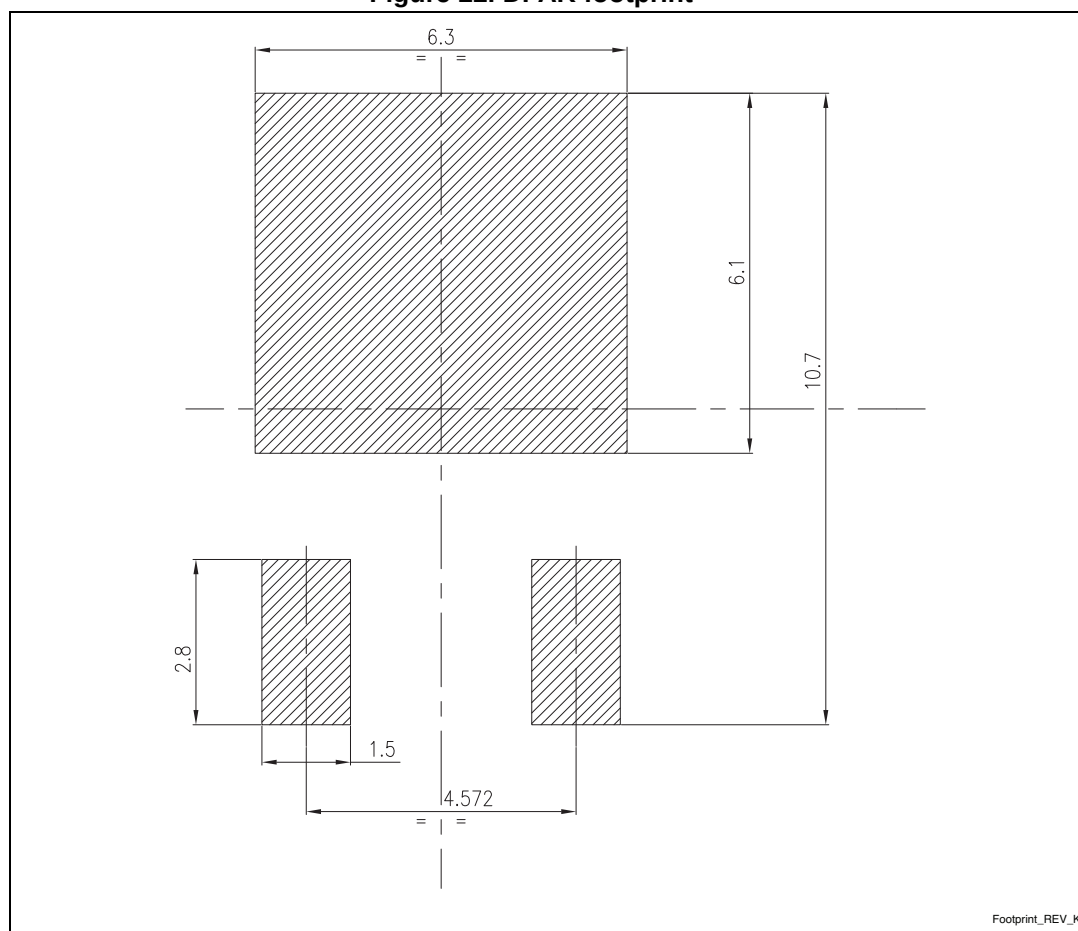


Figure 22. DPAK footprint (a)



a. All dimensions are in millimeters

5 Packaging mechanical data

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 23. Tape for DPAK (TO-252)

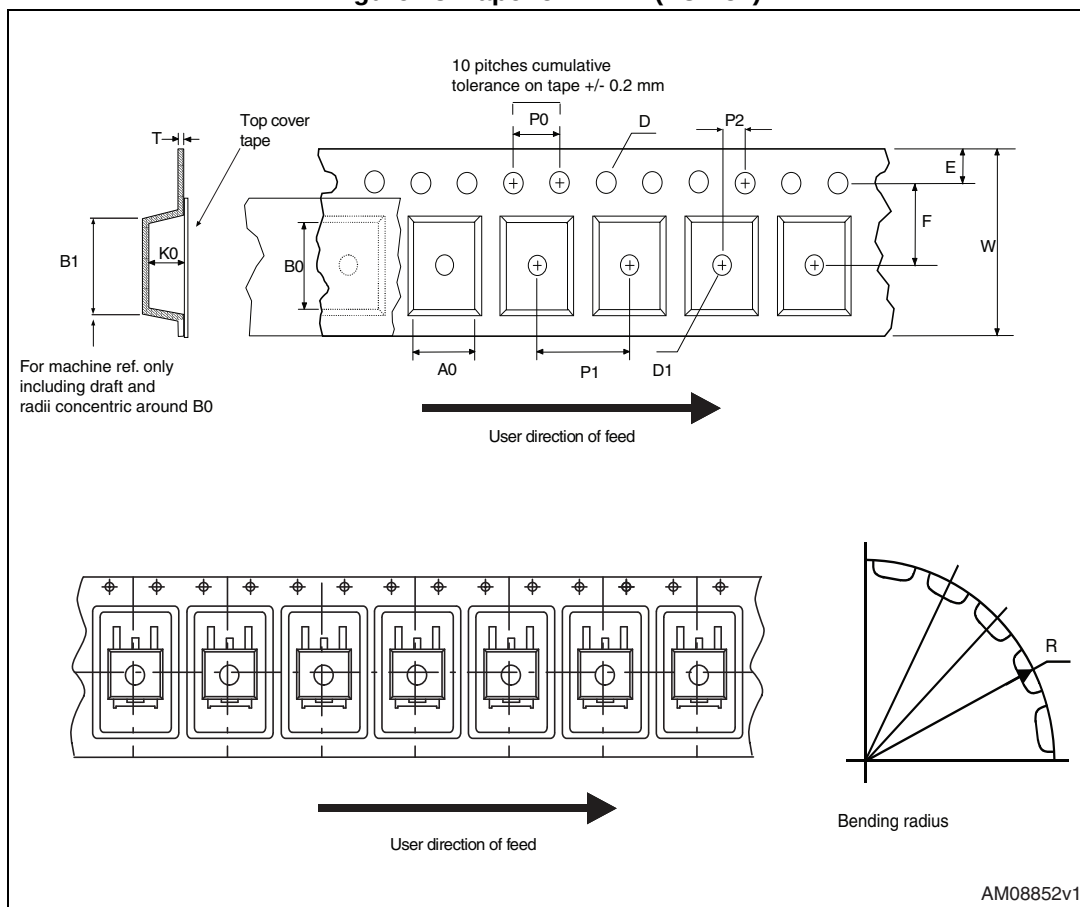
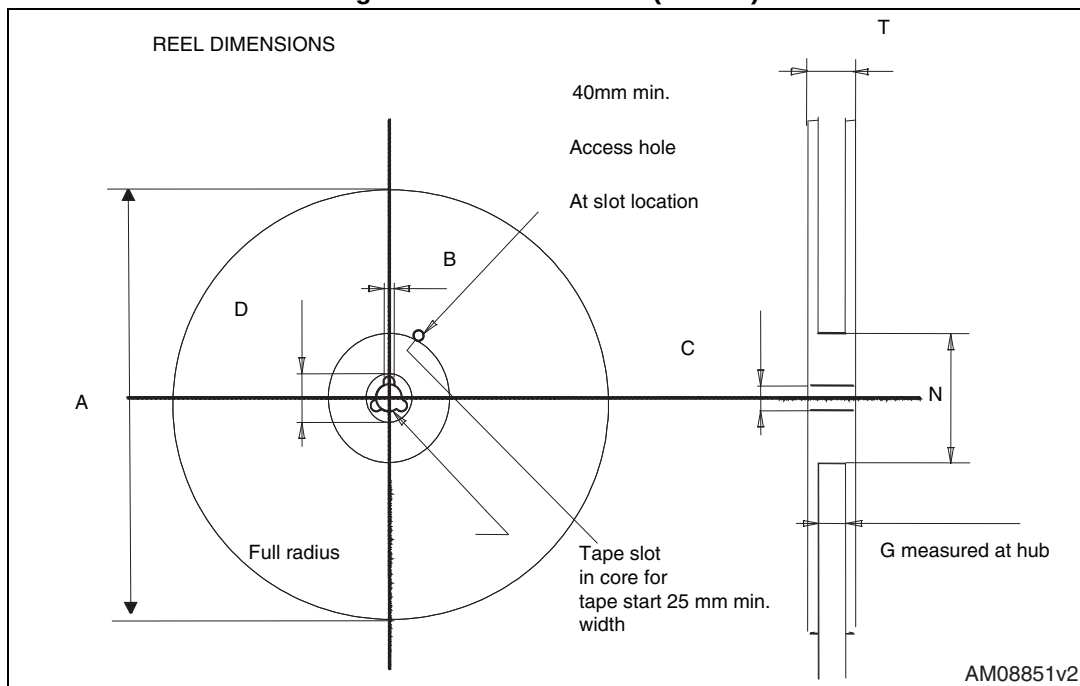


Figure 24. Reel for DPAK (TO-252)



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
19-Oct-2007	1	First release
23-Sep-2008	2	V _{GS} value has been changed on Table 2 and Table 5
20-Apr-2009	3	– Inserted typical maximum value in V_{GS(th)} parameter – Figure 5: Transfer characteristics has been updated – Added device in TO-220
05-Apr-2011	4	– Added device in Short IPAK – Added max values in Table 5: Dynamic – V_{GS} value has been changed in Table 2 and Table 4
09-Aug-2013	5	The part numbers STP60N3LH5, STU60N3LH5 and STU60N3LH5-S have been moved to a separate datasheet

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